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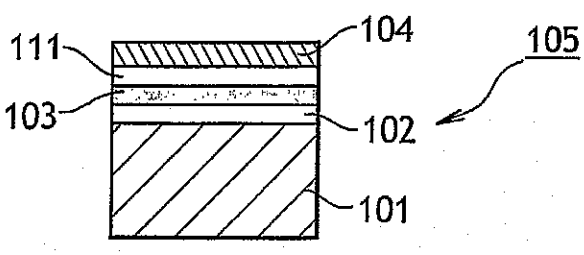
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(54) Title: HYBRID FULLY SOI-TYPE MULTILAYER STRUCTURE



(57) Abstract: The invention proposes a SOI-type multilayer structure (105), comprising a support layer (101), at least two working layers (103, 104) having different crystalline orientations, an insulating layer (102) extending over at least a portion of said support layer (101), characterized in that said insulating layer (102) extends over the whole surface of said support layer (101), so as to extend between said support layer (101) and said working layers (103, 104). A process for manufacturing such a structure (105) is also provided.